

- Ideal for European 858.25 MHz Transmitters
- Very Low Series Resistance
- **Quartz Stability**
- Surface-Mount Ceramic Case with 21 mm² Footprint
- Complies with Directive 2002/95/EC (RoHS)

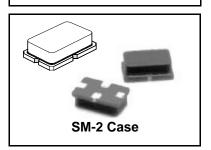
The RO2165A is a true one-port, surface-acoustic-wave (SAW) resonator in a surface-mount ceramic case. It provides reliable, fundamental-mode, quartz frequency stabilization of local oscillators operating at 858.25 MHz. This SAW is designed for remote-control and wireless security receivers operating under ETSI-ETS 300 220 in Europe and under FTZ 17 TR 2100 in Germany

Absolute Maximum Ratings

Rating	Value	Units	
CW RF Power Dissipation	+0	dBm	
DC Voltage Between Terminals	±30	VDC	
Case Temperature	-40 to +85	°C	
Soldering Temperature (10 seconds / 5 cycles max.)	260	°C	

RO2165A RO2165A-1 RO2165A-2

858.25 MHz SAW Resonator



Electrical Characteristics

CI	naracteristic	Sym	Notes	Minimum	Typical	Maximum	Units
Frequency (+25 °C) Nomina	l Frequency RO2165A			858.175		858.325	
	RO2165A-1	$f_{\mathbb{C}}$		858.175		858.475	MHz
	RO2165A-2		2, 3, 4, 5	858.150		858.350	
Tolerance from 858.25 MHz RO2165A						±75	
	RO2165A-1	Δf_{C}		-75		+225	kHz
	RO2165A-2				±100		
Insertion Loss		IL	2, 5, 6		1.1	2.0	dB
Quality Factor	Unloaded Q	Q _U	5.0.7		38,997		
	50 Ω Loaded Q	Q_L	5, 6, 7		4,000		
Temperature Stability	Turnover Temperature	T _O		15	30	45	°C
	Turnover Frequency	f _O	6, 7, 8		f _C		
	Frequency Temperature Coefficient	FTC			0.032		ppm/°C ²
Frequency Aging	Absolute Value during the First Year	fA	1		10		ppm/yr
DC Insulation Resistance be	tween Any Two Terminals		5	5 1.0 MΩ		ΜΩ	
RF Equivalent RLC Model	Motional Resistance	R_{M}			11		Ω
	Motional Inductance	L_M	5, 7, 9, 6		82.654		μH
	Motional Capacitance	C_{M}			0.4161		fF
	Shunt Static Capacitance	Co	5, 6, 9	2.6	2.9	3.2	pF
Test Fixture Shunt Inductance		L _{TEST}	2, 7		11.8581		nH
Lid Symbolization (in Additio	Symbolization (in Addition to Lot and/ or Date Code) 261				·		

without notice.

CAUTION: Electrostatic Sensitive Device. Observe precautions for handling. Notes:

- Frequency aging is the change in f_C with time and is specified at +65°C or less. Aging may exceed the specification for prolonged temperatures above +65°C. Typically, aging is greatest the first year after manufacture, decreasing in subsequent years.
- The center frequency, f_{C} , is measured at the minimum insertion loss point, IL_{MIN} , with the resonator in the 50 Ω test system (VSWR \leq 1.2:1). The shunt inductance, L_{TEST}, is tuned for parallel resonance with $\rm C_O$ at $\rm f_C$. Typically, $\rm f_{OSCILLATOR}$ or $\rm f_{TRANSMITTER}$ is approximately equal to the resonator f_C .
- One or more of the following United States patents apply: 4,454,488 and 4,616,197.
- Typically, equipment utilizing this device requires emissions testing and government approval, which is the responsibility of the equipment manufacturer.
- Unless noted otherwise, case temperature T_C = +25°C±2°C. The design, manufacturing process, and specifications of this device are subject to change
- Derived mathematically from one or more of the following directly measured parameters: f_C, IL, 3 dB bandwidth, f_C versus T_C, and C_O.
- Turnover temperature, T_O, is the temperature of maximum (or turnover) frequency, f_O. The nominal frequency at any case temperature, T_C , may be calculated from: $f = f_O$ [1 - FTC (T_O - $T_C)^2$]. Typically oscillator T_O is approximately equal to the specified resonator T_O .
- This equivalent RLC model approximates resonator performance near the resonant frequency and is provided for reference only. The capacitance C_O is the static (nonmotional) capacitance between the two terminals measured at low frequency (10 MHz) with a capacitance meter. The measurement includes parasitic capacitance with "NC" pads unconnected. Case parasitic capacitance is approximately 0.05 pF. Transducer parallel capacitance can by calculated as: $C_P \approx C_O - 0.05 \text{ pF}$.

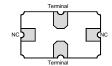
RF Monolithics, Inc. Fax: (972) 387-8148 Phone: (972) 233-2903 RFM Europe Phone: 44 1963 251383 Fax: 44 1963 251510 ©1999 by RF Monolithics, Inc. The stylized RFM logo are registered trademarks of RF Monolithics, Inc.

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SAW Resonator

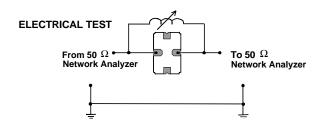
Electrical Connections

The SAW resonator is bidirectional and may be installed with either orientation. The two terminals are interchangeable and unnumbered. The callout NC indicates no internal connection. The NC pads assist with mechanical positioning and stability. External grounding of the NC pads is recommended to help reduce parasitic capacitance in the circuit

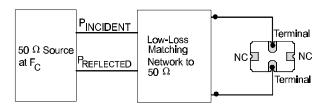


Typical Test Circuit

The test circuit inductor, L_{TEST} , is tuned to resonate with the static capacitance, C_{O} , at F_{C} .

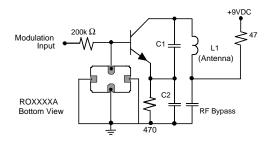


POWER TEST

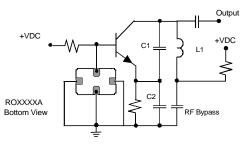


CW RF Power Dissipation = P_{INCIDENT} - P_{REFLECTED} **Typical Application Circuits**

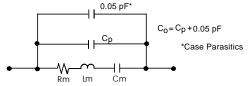
Typical Low-Power Transmitter Application



Typical Local Oscillator Application

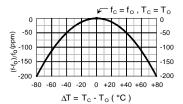


Equivalent LC Model



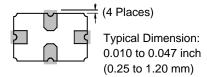
Temperature Characteristics

The curve shown on the right accounts for resonator contribution only and does not include LC component temperature contributions.



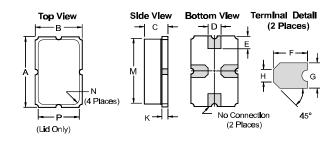
Typical Circuit Board Land Pattern

The circuit board land pattern shown below is one possible design. The optimum land pattern is dependent on the circuit board assembly process which varies by manufacturer. The distance between adjacent land edges should be at a maximum to minimize parasitic capacitance. Trace lengths from terminal lands to other components should be short and wide to minimize parasitic series inductances.



Case Design

The case material is black alumina with contrasting symbolization. All pads are nominally centered with respect to the base and consist of 40 to 70 microinches electroless gold on 60-350 microinches electroless nickel.



Dimensions	Millimeters		Inches		
	Min	Max	Min	Max	
A	5.74	5.99	0.226	0.236	
В	3.73	3.99	0.147	0.157	
С	1.91	2.16	0.075	0.085	
D	0.94	1.10	0.037	0.043	
Е	0.83	1.20	0.033	0.047	
F	1.16	1.53	0.046	0.060	
G	0.94	1.10	0.037	0.043	
Н	0.43	0.59	0.017	0.023	
K	0.43	0.59	0.017	0.023	
М	5.08	5.33	0.200	0.210	
N	0.38	0.64	0.015	0.025	
Р	3.05	3.30	0.120	0.130	